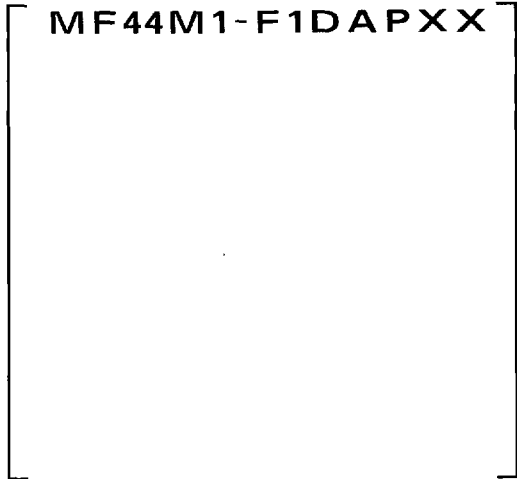


16-bit Data Bus
One-Time PROM Card



Connector Type

Two-piece 60-pin

DESCRIPTION

Mitsubishi's One-Time PROM cards provide large memory capacities on a device approximately the size of a credit card (85.6mm × 54mm × 3.4mm). The cards use a 16-bit data bus. Available in 4M byte capacities, Mitsubishi's One-Time PROM cards are available with a 60 pin, two-piece connector.

FEATURES

- Uses TSOP (Thin Small Outline Package) to achieve very high memory density coupled with high reliability, without enlarging card size
- Electrostatic discharge protection to 25kV
- Buffered interface
- 60-pin connector
- 16-bit data width

APPLICATIONS

- Office automation
- Computers
- Telecommunications
- Data Communications
- Industrial
- Consumer

PRODUCT LIST

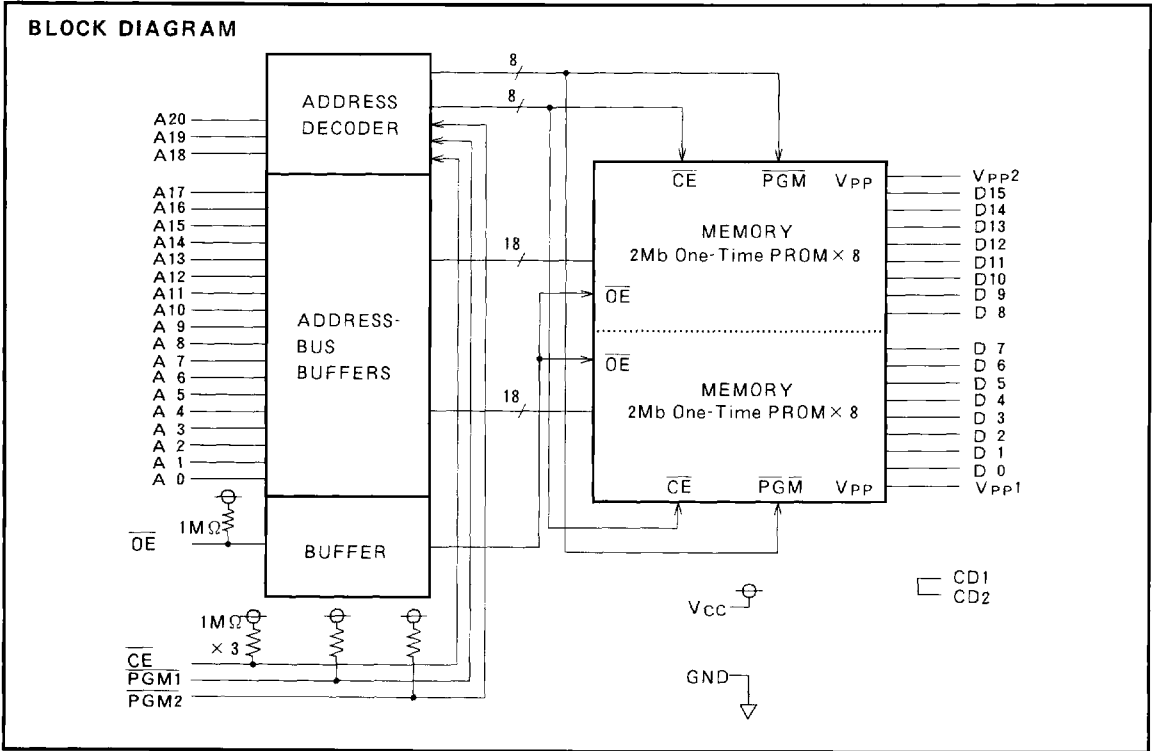
Type name	Item	Memory capacity	Data bus width (bits)	Access time (ns)	Connector type	Number of pins	Outline drawing
MF44M1-F1DAPXX		4MB	16	200	Two-piece	60	60P-001

ONE-TIME PROM CARDS

PIN ASSIGNMENT

Two Piece Type (60-pin)

Pin No.	Symbol	Function	Pin No.	Symbol	Function
1	NC	No connection	2	NC	No connection
3	V _{PP} 1	Power supply 1	4	V _{PP} 2	Power supply 2
5	A12	Address input	6	CD 1	Card detect 1
7	A 7		8	A15	Address input
9	A 6		10	A16	
11	A 5		12	A17	
13	A 4		14	A18	
15	A 3		16	A19	
17	A 2		18	A20	No connection
19	A 1		20	NC	
21	A 0	Data I/O	22	NC	Data I/O
23	D 0		24	D 8	
25	D 1		26	D 9	
27	D 2	Ground	28	D10	Date I/O
29	GND		30	GND	
31	D 3	Data I/O	32	GND	Ground
33	D 4		34	D11	
35	D 5		36	D12	Date I/O
37	D 6		38	D13	
39	D 7		40	D14	
41	\overline{CE}	Card enable	42	D15	No connection
43	A10	Address input	44	NC	
45	\overline{OE}	Output enable	46	PGM 2	Program control 2
47	A11	Address input	48	NC	No connection
49	A 9		50	NC	
51	A 8		52	B 0	GND
53	A13		54	B 1	No connection
55	A14	Program control 1	56	B 2	GND
57	PGM 1		58	CD 2	Card detect 2
59	V _{CC}	Power supply	60	V _{CC}	Power supply



FUNCTION TABLE

Mode	CE	OE	PGM(Notes 1)	V _{PP} (typ.)	V _{CC} (typ.)	I/O	I _{CC}
Standby	H	X	X	5 V	5 V	High-impedance	Standby
Read	L	L	X	5 V	5 V	Data out	Active
Output disable	L	H	X	5 V	5 V	High-impedance	Active
Word Program	L	H	L	12.5V	6 V	Data in	Active
Program verify	L	L	H	12.5V	6 V	Data out	Active
Page data latch	H	L	H	12.5V	6 V	Data in	Active
Page program	H	H	L	12.5V	6 V	High-impedance	Active
Program inhibit	X	L	L	12.5V	6 V	High-impedance	Active
	X	H	H	12.5V	6 V	High-impedance	Active

Note 1 : PGM = PGM1 + PGM2

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{CC}	Supply voltage	With respect to GND	-0.5~7.0	V
V _{PP}	Supply voltage		-0.5~14.0	V
V _I	Input voltage		-0.5~V _{CC} +0.5 (7.0Max.)	V
V _O	Output voltage		0~V _{CC}	V
T _{opr}	Operating temperature		0~70	°C
T _{stg1}	Storage temperature 1		-40~80	°C

ONE-TIME PROM CARDS

READ OPERATION

RECOMMENDED OPERATING CONDITIONS ($T_a = 0 \sim 50^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Limits			Unit
		Min.	Typ.	Max.	
V_{CC}	V_{CC} supply voltage	4.5	5.0	5.5	V
V_{PP}	V_{PP} supply voltage		V_{CC}		V
V_{IH}	High input voltage	$0.7 \times V_{CC}$		V_{CC}	V
V_{IL}	Low input voltage	0		0.8	V

ELECTRICAL CHARACTERISTICS ($T_a = 0 \sim 50^\circ\text{C}$, $V_{CC} = V_{PP} = 4.5 \sim 5.5\text{V}$, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{OH}	High output voltage	$I_{OH} = -400 \mu\text{A}$	2.4			V
V_{OL}	Low output voltage	$I_{OL} = 2.1\text{mA}$			0.45	V
I_{IH}	High input current	$V_i = V_{CC}$ V			10	μA
I_{iL}	Low input current	$V_i = 0$ V	\overline{CE} OE PGM 1 PGM 2		-20	μA
			Other inputs		-10	
I_{OZH}	High output current in off state	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$, $V_O = V_{CC}$ V			10	μA
I_{OZL}	Low output current in off state	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$, $V_O = 0$ V			-10	μA
$I_{CC1 \cdot 1}$	Standby V_{CC} supply current	$\overline{CE} = V_{IH}$, outputs=open, Other inputs= V_{IH} or V_{iL}			65	mA
$I_{CC1 \cdot 2}$	Standby V_{CC} supply current	$\overline{CE} \geq V_{CC} - 0.2\text{V}$, Output=open, Other inputs $\leq 0.2\text{V}$ or $\geq V_{CC} - 0.2\text{V}$			5	mA
$I_{CC2 \cdot 1}$	Active V_{CC} supply current (Minimum cycle)	$\overline{CE} = \overline{OE} = V_{iL}$, Outputs=open, Other inputs= V_{IH} or V_{iL}			180	mA
$I_{CC2 \cdot 2}$	Active V_{CC} supply current (Minimum cycle)	$\overline{CE} = \overline{OE} \leq 0.2\text{V}$, Outputs=open, Other inputs $\leq 0.2\text{V}$ or $\geq V_{CC} - 0.2\text{V}$			130	mA
I_{PP1}	V_{PP} supply current of each V_{PP} pin (V_{PP1} or V_{PP2})				1.0	mA

Note 2 : Direction for current flowing into IC is indicated as positive (no mark).

ONE-TIME PROM CARDS

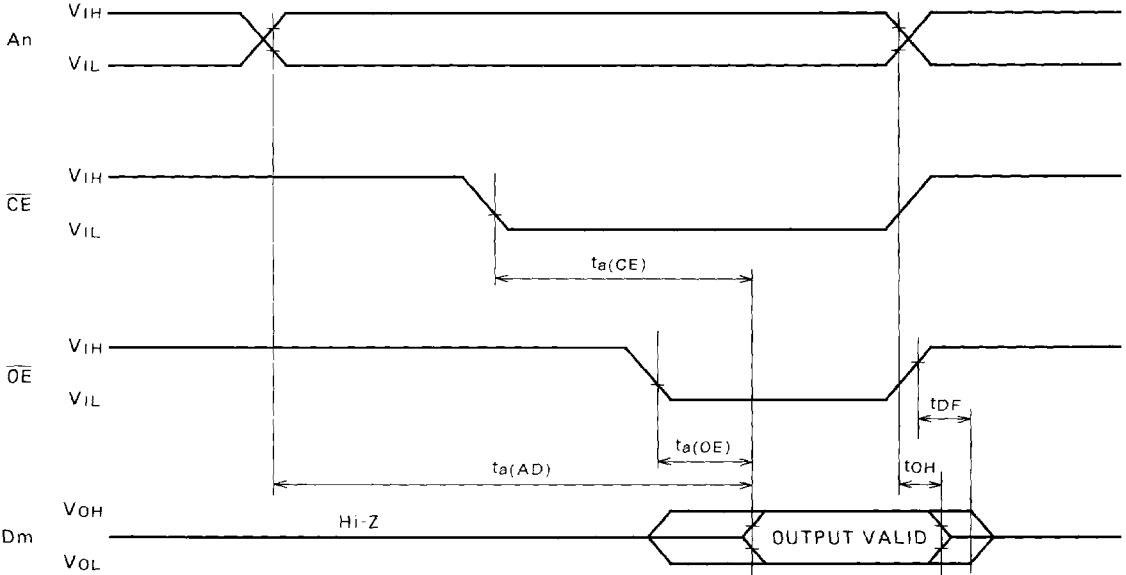
SWITCHING CHARACTERISTICS

Read Cycle (Ta = 0 ~ 50°C, VCC = VPP = 4.5 ~ 5.5V, unless otherwise noted)

Symbol	Parameter	Conditions	Limits			Unit
			Min.	Typ.	Max.	
ta(AD)	Address access time	$\overline{CE} = \overline{OE} = V_{IL}$			200	ns
ta(CE)	Card select access time	$\overline{OE} = V_{IL}$			200	ns
ta(OE)	Output enable access time	$\overline{CE} = V_{IL}$			100	ns
tDF	Output disable time (from \overline{OE})	$\overline{CE} = V_{IL}$	0		100	ns
tOH	Data hold time after address change	$\overline{CE} = \overline{OE} = V_{IL}$	0			ns

Note 3 : VCC must be applied simultaneously VPP and removed simultaneously VPP.

TIMING DIAGRAM (READ OPERATION)



Note 4 : Test conditions
 Input pulse levels : $V_{IL} = 0.45 V, V_{IH} = 0.8 \times V_{CC} V$
 Input pulse rise, fall time : $t_r = t_f = 10ns$
 Reference voltage input : $V_{IL} = 0.8 V, V_{IH} = 0.7 \times V_{CC} V$
 output : $V_{OL} = 0.8 V, V_{OH} = 2.0 V$
 (tDF is measured when output voltage is $\pm 500mV$ from steady state.)
 Load : 100pF + 1TTL gate
 : 5pF + 1TTL gate (at tDF measuring)



ONE-TIME PROM CARDS

PROGRAM OPERATION

RECOMMENDED OPERATING CONDITIONS ($T_a=20\sim 30^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Limits			Unit
		Min.	Typ.	Max.	
V _{CC}	V _{CC} supply voltage	5.75	6.0	6.25	V
V _{PP}	V _{PP} supply voltage	12.2	12.5	12.8	V
V _{IH}	High input voltage	0.7 × V _{CC}			V
V _{IL}	Low input voltage	0			V

ELECTRICAL CHARACTERISTICS ($T_a=20\sim 30^\circ\text{C}$, V_{CC}=5.75~6.25V, V_{PP}=12.2~12.8V, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{OH}	High output voltage	I _{OH} = -400 μA	2.4			V
V _{OL}	Low output voltage	I _{OL} = 2.1mA			0.45	V
I _{IH}	High input current	V _I = V _{CC} V			10	μA
I _{IL}	Low input current	V _I = 0 V			-20	μA
		CE, OE, PGM 1, PGM 2 Other inputs			-10	
I _{CC 3-1}	Active V _{CC} supply current	Inputs = V _{IH} or V _{IL} , Outputs = open			620	mA
I _{CC 3-2}	Active V _{CC} supply current	Inputs ≤ 0.2V or ≥ V _{CC} - 0.2V, Outputs = open			560	mA
I _{CC 2-1}	V _{PP} supply current of each V _{PP} pin (V _{PP} 1 or V _{PP} 2)	CE = V _{IL} <WORD PROGRAM>			60	mA
I _{CC 2-2}		CE = V _{IH} <PAGE PROGRAM>			130	mA

Note 5 : Direction for current flowing into IC is indicated as positive (no mark).

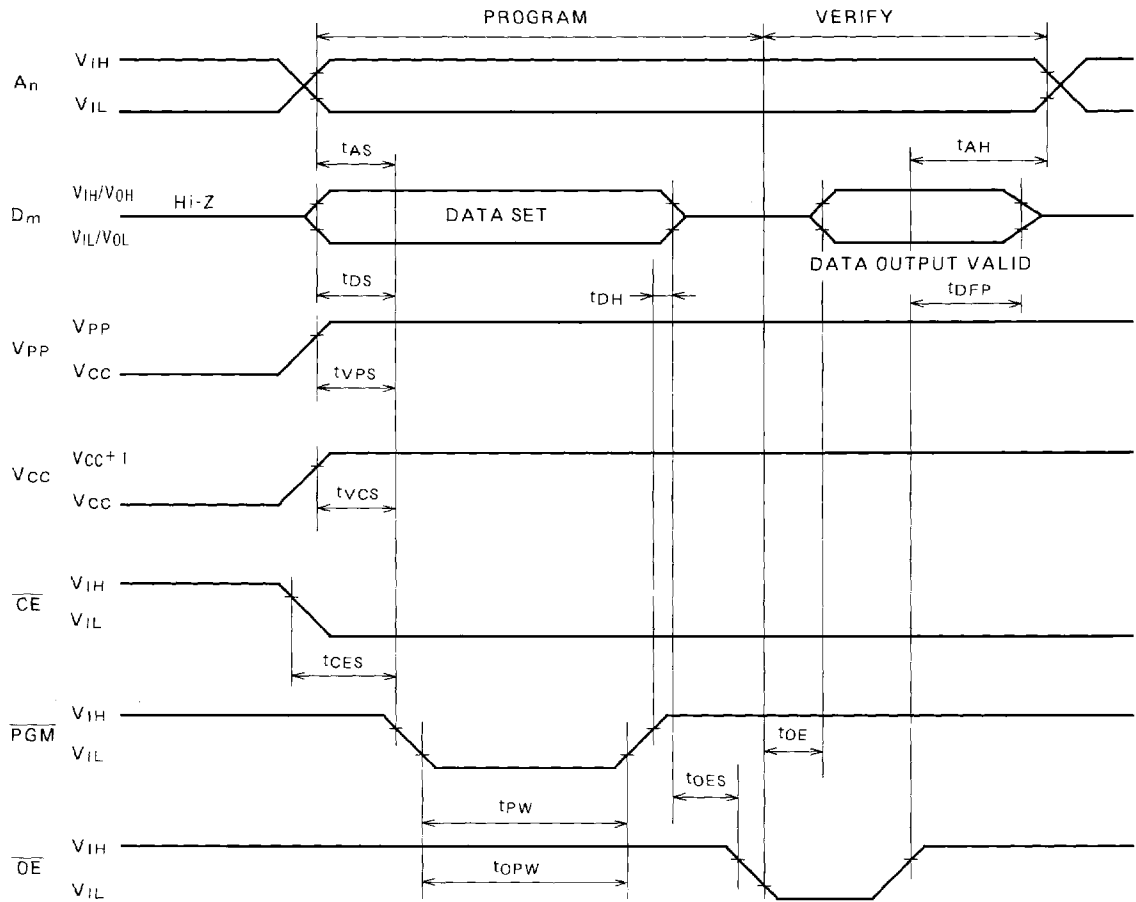
WORD PROGRAM

SWITCHING CHARACTERISTICS ($T_a=20\sim 30^\circ\text{C}$, V_{CC}=5.75~6.25V, V_{PP}=12.2~12.8V, unless otherwise noted)

Symbol	Parameter	Limits			Unit
		Min.	Typ.	Max.	
t _{AS}	Address setup time	2			μs
t _{OES}	OE setup time	2			μs
t _{DS}	Data setup time	2			μs
t _{AH}	Address hold time	0			μs
t _{DH}	Data hold time	2			μs
t _{DFP}	Output disable time (from OE)	0		180	ns
t _{VCS}	V _{CC} setup time	2			μs
t _{VPS}	V _{pp} setup time	2			μs
t _{PW}	PGM initial program pulse width	0.19	0.2	0.21	ms
t _{OPW}	PGM over program pulse width	0.19		5.25	ms
t _{CES}	CE setup time	2			μs
t _{OE}	Data valid from OE			200	ns

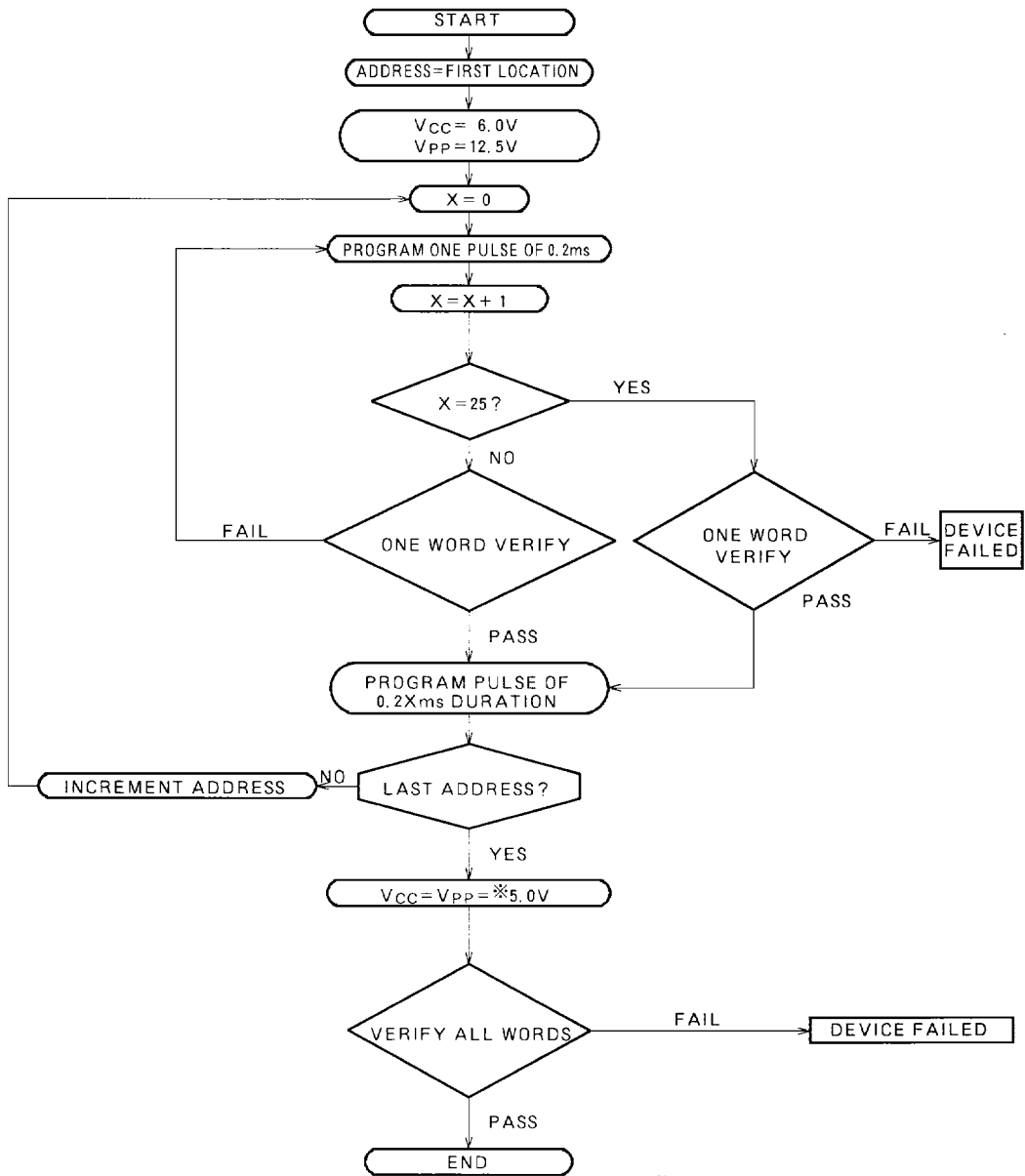
Note 6 : V_{CC} must be applied simultaneously V_{PP} and removed simultaneously V_{PP}.

**WORD PROGRAM
TIMING DIAGRAM (PROGRAM OPERATION)**



Note 7 : Test conditions
 Input pulse levels : $V_{IL} = 0.45 V, V_{IH} = 0.8 \times V_{CC} V$
 Input pulse rise, fall time : $t_r = t_f = 10 ns$
 Reference voltage input : $V_{IL} = 0.8 V, V_{IH} = 0.7 \times V_{CC} V$
 output : $V_{OL} = 0.8 V, V_{OH} = 2.0 V$
 (tDFP is measured when output voltage is $\pm 500 mV$ from steady steady state.)

WORD PROGRAMMING ALGORITHM FLOW CHART



※4.5V ≤ V_{CC} = V_{PP} ≤ 5.5V

ONE-TIME PROM CARDS

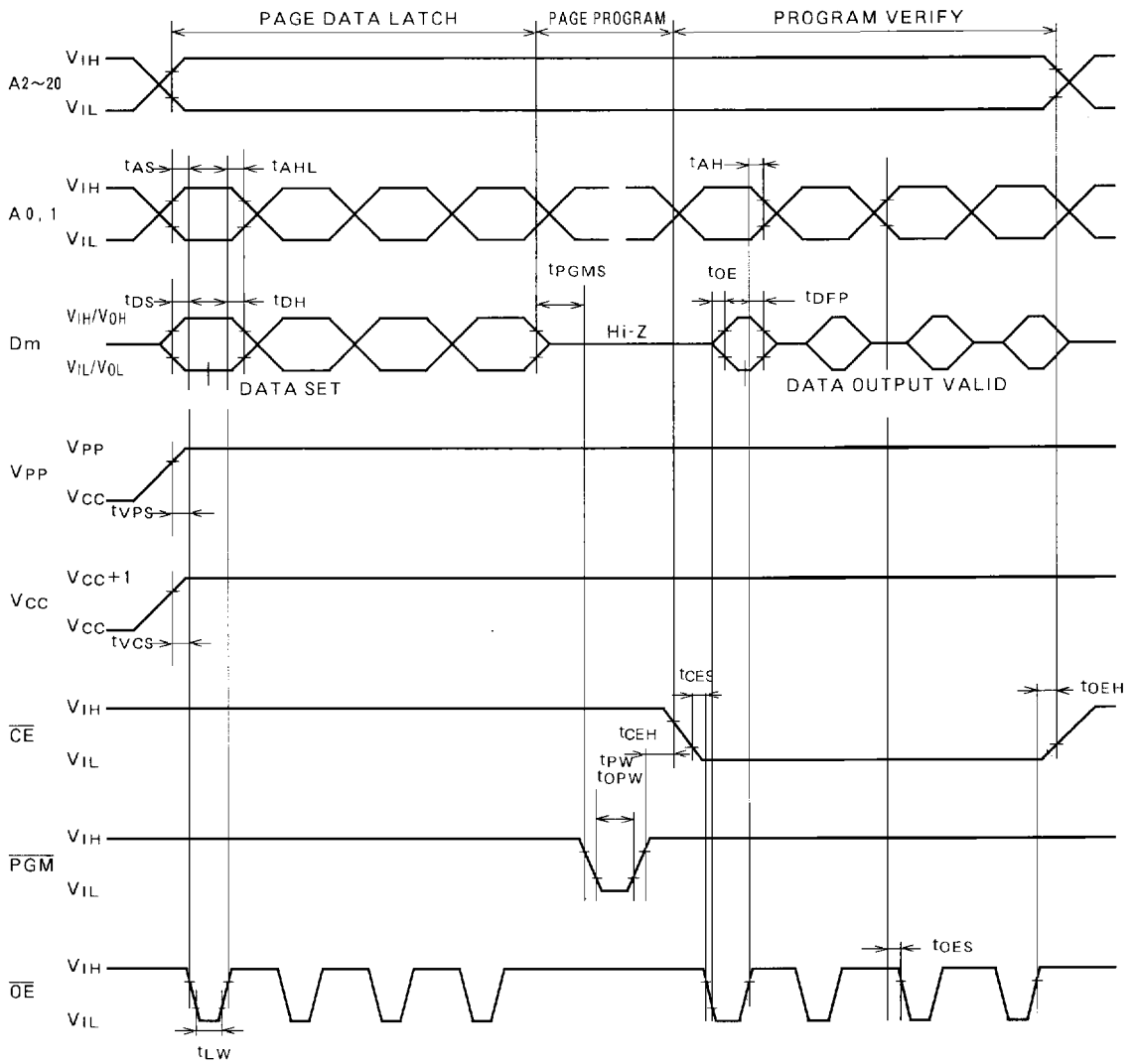
PAGE PROGRAM

SWITCHING CHARACTERISTICS (T_a=20~30°C, V_{CC}=5.75~6.25V, V_{PP}=12.2~12.8V, unless otherwise noted)

Symbol	Parameter	Limits			Unit
		Min.	Typ.	Max.	
tAS	Address setup time	2			μs
tOES	OE setup time	2			μs
tDS	Data setup time	2			μs
tAH	Address hold time	0			μs
tAHL		2			μs
tDH	Data hold time	2			μs
tDFP	Output disable time (from OE)	0		180	ns
tVCS	V _{CC} setup time	2			μs
tVPS	V _{PP} setup time	2			μs
tPW	PGM initial program pulse width	0.19	0.20	0.21	ms
tOPW	PGM over program pulse width	0.19		5.25	ms
tCES	CE setup time	2			μs
tOE	Data valid from OE	0		200	ns
tLW	Data latch time	1			μs
tPGMS	PGM setup time	2			μs
tCEH	CE hold time	2			μs
tOEH	OE hold time	2			μs

Note 8 : V_{CC} must be applied simultaneously V_{PP} and removed simultaneously V_{PP}.

PAGE PROGRAM TIMING DIAGRAM (PROGRAM OPERATION)



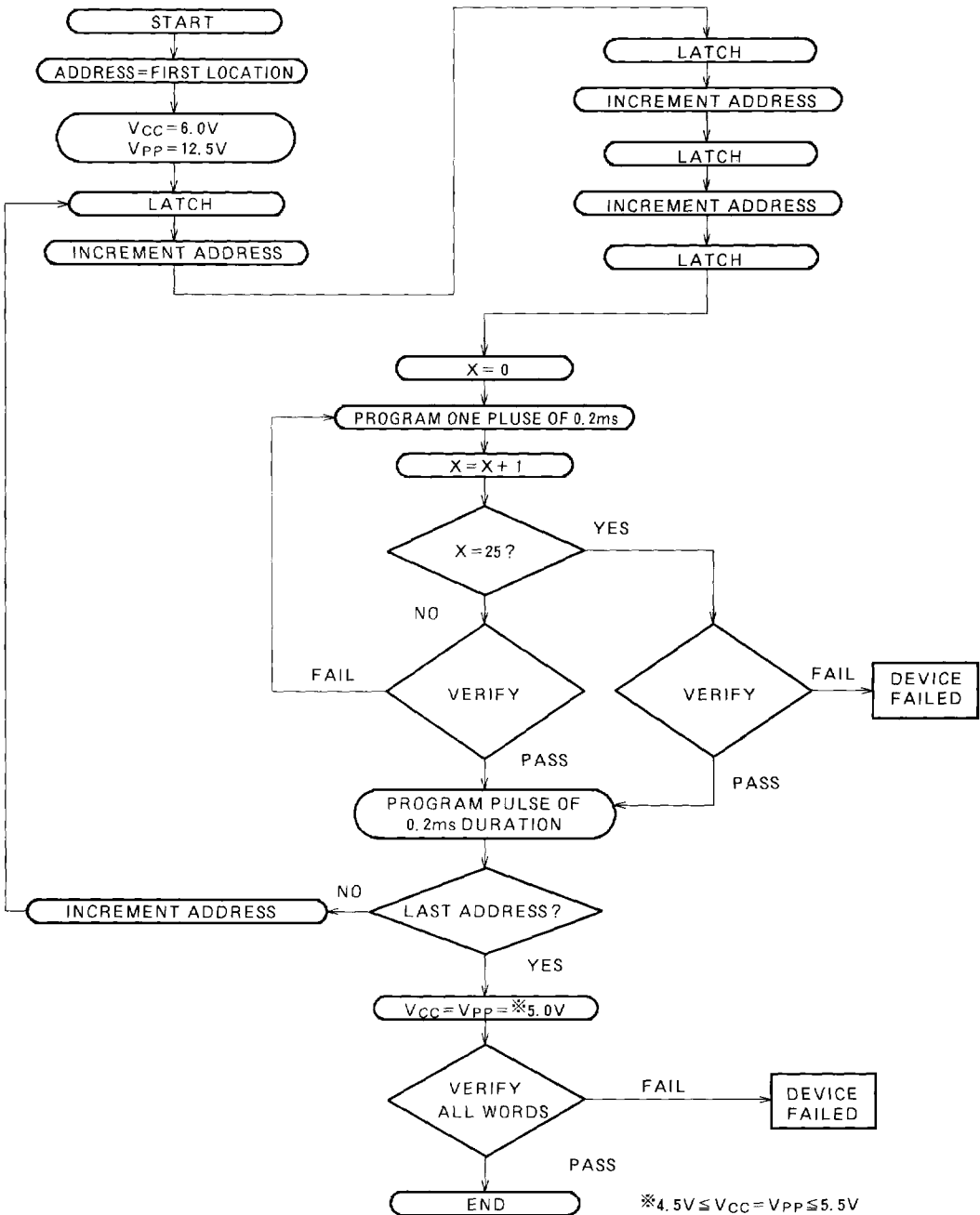
Note 9 : Test conditions

Input pulse levels : $V_{IL}=0.45$ V, $V_{IH}=0.8 \times V_{CC}$ V

Input pulse rise, fall time : $t_r = t_f = 10$ ns

Reference voltage input : $V_{IL}=0.8$ V, $V_{IH}=0.7 \times V_{CC}$ V (tDFO is measured when output voltage is ± 500 mV from steady state.)
 output : $V_{IL}=0.8$ V, $V_{IH}=2.0$ V

PAGE PROGRAMMING ALGORITHM FLOW CHART



*4.5V ≤ VCC = VPP ≤ 5.5V



CAPACITANCE

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
C _I	Input capacitance	V _I = GND, V _I = 25mVrms, f = 1 MHz, T _a = 25°C			40	pF
C _O	Output capacitance	V _O = GND, V _O = 25mVrms, f = 1 MHz, T _a = 25°C			140	pF

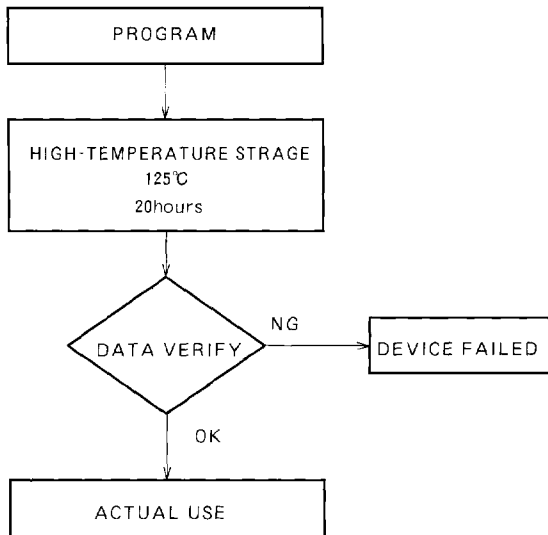
Note 10 : These items are not 100% tested.

DEVICE IDENTIFIER MODE

This card does not support a device identifier mode.
Do not apply voltages exceeding 7V to A9 pin.

RECOMMENDED SCREENING CONDITIONS

The following screening test is recommended before using for evaluation. If this card is used for other purpose, the program in manufacture is recommended.



Note 11 : The color of the panels might be affected at this high - temperature storage.
After the data - verify test, putting on your designed labels on the surface of the card is recommended.